

24. (New) A LED according to claim 7, wherein the insertion layer lowers a forward voltage between the p-type cladding layer and the window layer.

*Concluded  
B<sup>1</sup>*  
25. (New) An epitaxial wafer according to claim 8, wherein the insertion layer lowers a forward voltage between the p-type cladding layer and the p-type window layer.

26. (New) An expitaxial wafer according to claim 14, wherein the insertion layer lowers a forward voltage between the p-type cladding layer and the window layer.

27. (New) A LED according to claim 15, wherein the insertion layer lowers a forward voltage between the p-type cladding layer and the p-type window layer.

28. (New) An epitaxial wafer according to claim 19, wherein the insertion layer lowers a forward voltage between the p-type cladding layer and the p-type window layer.

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